

Arkka Bhattacharyya

List of Publications by Year in descending order

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Version: 2024-02-01

24
papers

692
citations

566801

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413
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#	ARTICLE	IF	CITATIONS
1	High-k Oxide Field-Plated Vertical (001) $\text{In}_2\text{Ga}_2\text{O}_3$ Schottky Barrier Diode With Baliga's Figure of Merit Over 1 GW/cm^2 . IEEE Electron Device Letters, 2021, 42, 1140-1143.	2.2	86
2	Low temperature homoepitaxy of (010) $\text{In}_2\text{-Ga}_2\text{O}_3$ by metalorganic vapor phase epitaxy: Expanding the growth window. Applied Physics Letters, 2020, 117, .	1.5	56
3	Multi-kV Class $\text{In}_2\text{-Ga}_2\text{O}_3$ MESFETs With a Lateral Figure of Merit Up to 355 MW/cm^2 . IEEE Electron Device Letters, 2021, 42, 1272-1275.	2.2	50
4	Ga_2O_3 -on-SiC Composite Wafer for Thermal Management of Ultrawide Bandgap Electronics. ACS Applied Materials & Interfaces, 2021, 13, 40817-40829.	4.0	49
5	Si-doped $\text{In}_2\text{-(Al}_{0.26}\text{Ga}_{0.74})_2\text{O}_3$ thin films and heterostructures grown by metalorganic vapor-phase epitaxy. Applied Physics Express, 2019, 12, 111004.	1.1	47
6	Degenerate doping in $\text{In}_2\text{-Ga}_2\text{O}_3$ single crystals through Hf-doping. Semiconductor Science and Technology, 2020, 35, 04LT01.	1.0	43
7	Growth and characterization of metalorganic vapor-phase epitaxy-grown $\text{In}_2\text{-(Al}_x\text{)}_2\text{O}_3$ channels. Applied Physics Express, 2021, 14, 025501.	1.1	40
8	4.4 kV $\text{In}_2\text{-Ga}_2\text{O}_3$ MESFETs with power figure of merit exceeding 100 MW cm^{-2} . Applied Physics Express, 2022, 15, 061001.	1.1	40
9	130 nm^2 $\text{In}_2\text{-Ga}_2\text{O}_3$ metal semiconductor field effect transistor with low-temperature metalorganic vapor phase epitaxy-regrown ohmic contacts. Applied Physics Express, 2021, 14, 076502.	1.1	39
10	Electrical and optical properties of Zr doped $\text{In}_2\text{-Ga}_2\text{O}_3$ single crystals. Applied Physics Express, 2019, 12, 085502.	1.1	38
11	Delta-doped $\text{In}_2\text{-Ga}_2\text{O}_3$ thin films and $\text{In}_2\text{-(Al}_{0.26}\text{Ga}_{0.74})_2\text{O}_3$ heterostructures grown by metalorganic vapor-phase epitaxy. Applied Physics Express, 2020, 13, 045501.	1.1	38
12	Schottky Barrier Height Engineering in $\text{In}_2\text{-Ga}_2\text{O}_3$ Using SiO_2 Interlayer Dielectric. IEEE Journal of the Electron Devices Society, 2020, 8, 286-294.	1.2	32
13	Design of a $\text{In}_2\text{-Ga}_2\text{O}_3$ Schottky Barrier Diode With p-Type III-Nitride Guard Ring for Enhanced Breakdown. IEEE Transactions on Electron Devices, 2020, 67, 4842-4848.	1.6	21
14	Delta-doped $\text{In}_2\text{-Ga}_2\text{O}_3$ films with narrow FWHM grown by metalorganic vapor-phase epitaxy. Applied Physics Letters, 2020, 117, .	1.5	17
15	In Situ Dielectric Al_2O_3 $\text{In}_2\text{-Ga}_2\text{O}_3$ Interfaces Grown Using Metal-Organic Chemical Vapor Deposition. Advanced Electronic Materials, 2021, 7, 2100333.	2.6	17
16	Synthesis and Characterization of Large-Area Nanometer-Thin $\text{In}_2\text{-Ga}_2\text{O}_3$ Films from Oxide Printing of Liquid Metal Gallium. Physica Status Solidi (A) Applications and Materials Science, 2020, 217, 1901007.	0.8	16
17	N-type doping of low-pressure chemical vapor deposition grown $\text{In}_2\text{-Ga}_2\text{O}_3$ thin films using solid-source germanium. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2021, 39, .	0.9	14
18	Compensation in (201) homoepitaxial $\text{In}_2\text{-Ga}_2\text{O}_3$ thin films grown by metalorganic vapor-phase epitaxy. Journal of Applied Physics, 2020, 128, .	1.1	13

#	ARTICLE	IF	CITATIONS
19	Defect states and their electric field-enhanced electron thermal emission in heavily Zr-doped In^{2+} -Ga ₂ O ₃ crystals. Applied Physics Letters, 2020, 117, .	1.5	13
20	Oxygen annealing induced changes in defects within In^{2+} -Ga ₂ O ₃ epitaxial films measured using photoluminescence. Journal Physics D: Applied Physics, 2021, 54, 174004.	1.3	11
21	Electronic and ionic conductivity in In^{2+} -Ga ₂ O ₃ single crystals. Journal of Applied Physics, 2022, 131, .	1.1	5
22	Spalling-Induced Liftoff and Transfer of Electronic Films Using a van der Waals Release Layer. Small, 2021, 17, e2102668.	5.2	4
23	On the terahertz response of metal-gratings on anisotropic dielectric substrates and its prospective application for anisotropic refractive index characterization. Journal of Applied Physics, 2022, 131, .	1.1	3
24	Lateral Gallium Oxide Field Effect Transistors with High Figure of Merit. , 2022, , .		0